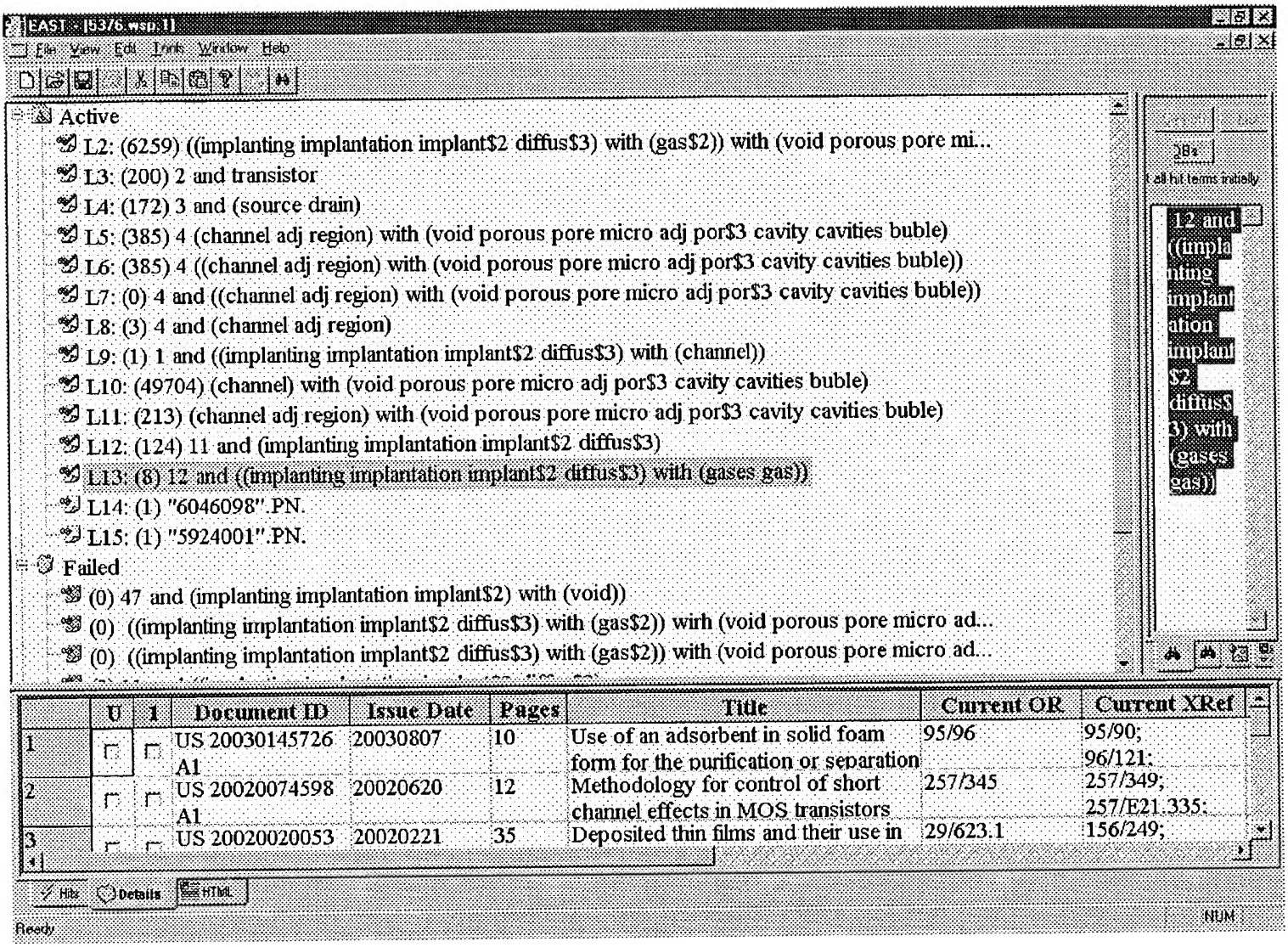
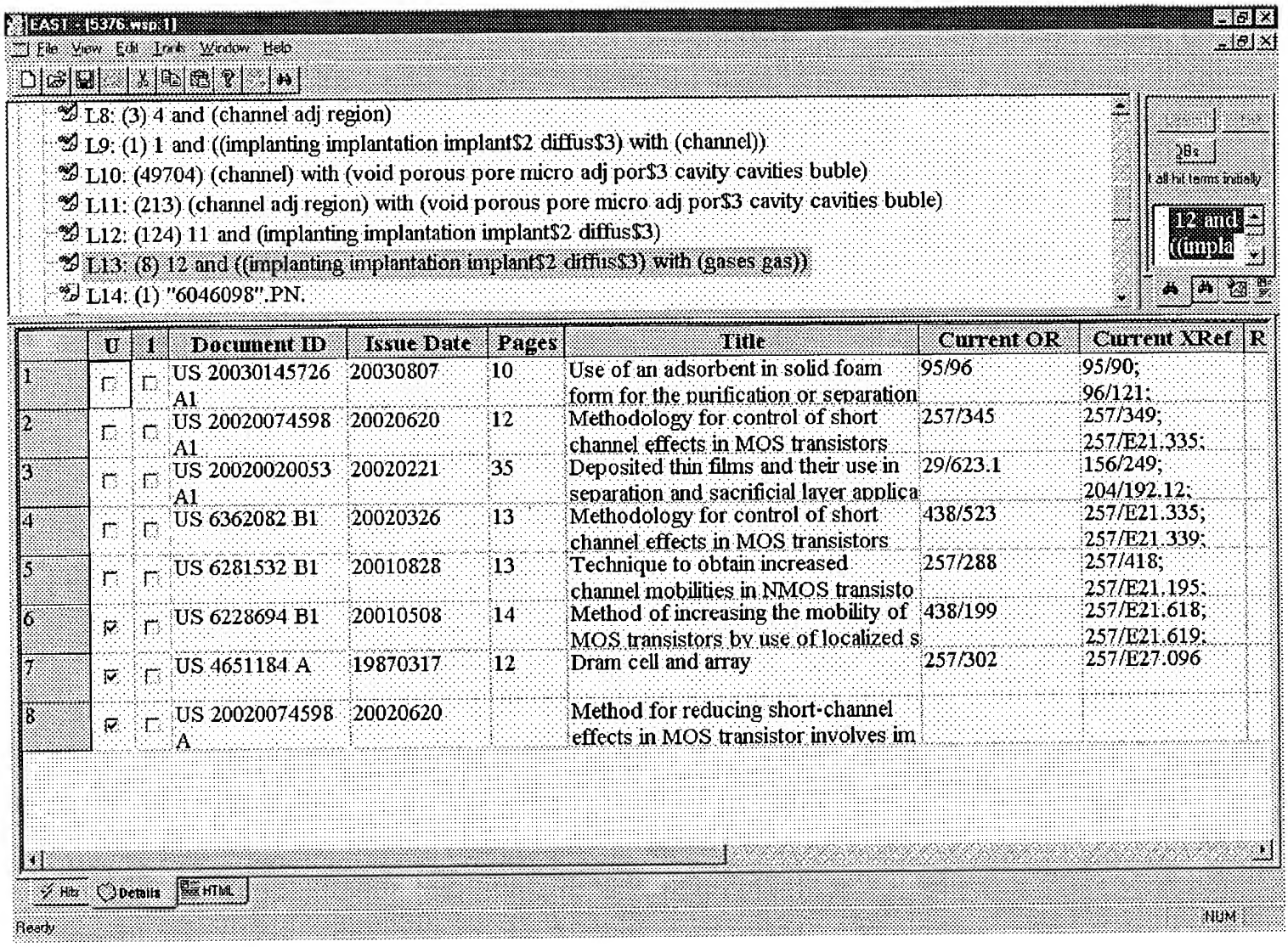


	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	☐	☐	US 20030145726 A1	20030807	10	Use of an adsorbent in solid foam form for the purification or separation	95/96	95/90; 96/121;
2	☐	☐	US 20020074598 A1	20020620	12	Methodology for control of short channel effects in MOS transistors	257/345	257/349; 257/E21.335;
3	☐	☐	US 20020020053	20020221	35	Deposited thin films and their use in	29/623.1	156/249;



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3	☐	☐	US 20020020053 A1	20020221	35	Deposited thin films and their use in separation and sacrificial layer applica	29/623.1	156/249; 204/192.12;	
4	☐	☐	US 6362082 B1	20020326	13	Methodology for control of short channel effects in MOS transistors	438/523	257/E21.335; 257/E21.339;	
5	☐	☐	US 6281532 B1	20010828	13	Technique to obtain increased channel mobilities in NMOS transisto	257/288	257/418; 257/E21.195;	
6	☑	☐	US 6228694 B1	20010508	14	Method of increasing the mobility of MOS transistors by use of localized s	438/199	257/E21.618; 257/E21.619;	
7	☑	☐	US 4651184 A	19870317	12	Dram cell and array	257/302	257/E27.096	
8	☑	☐	US 20020074598 A	20020620		Method for reducing short-channel effects in MOS transistor involves im			